**100V N- Channel SGT Power MOSFET**

## MAIN CHARACTERISTICS

| | |
|---|---|
| $I_D$ | 50A |
| $V_{DS}$ | 100V |
| $R_{DSON}$-typ(@$V_{GS}$=10V) | 20mΩ**(Typ:14mΩ)** |

## Features

- YFW-SGT technology
- Ultra-Low RDS(ON)
- Low Gate Charge
- High Curreeg e

## Ratings and Characteristic Curves

Figure 1: Power De-rating

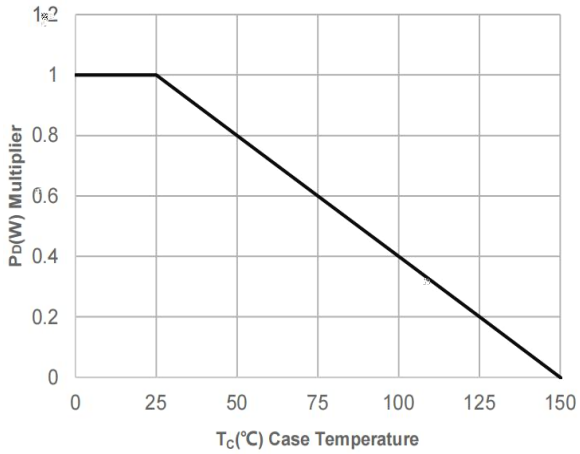



Figure 2: Current De-rating

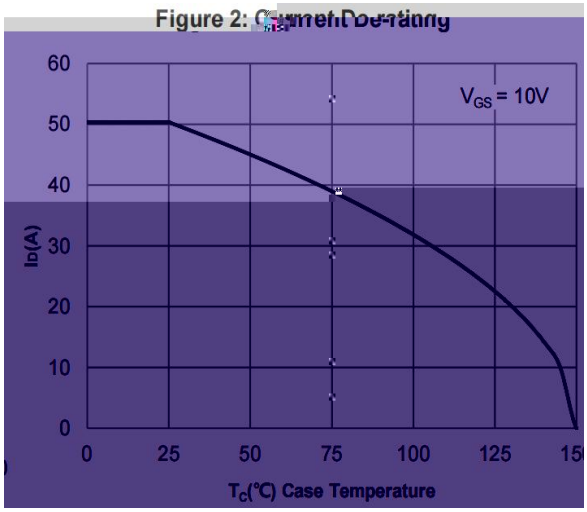



Figure 3: Normalized Maximum Transient Thermal Impedance

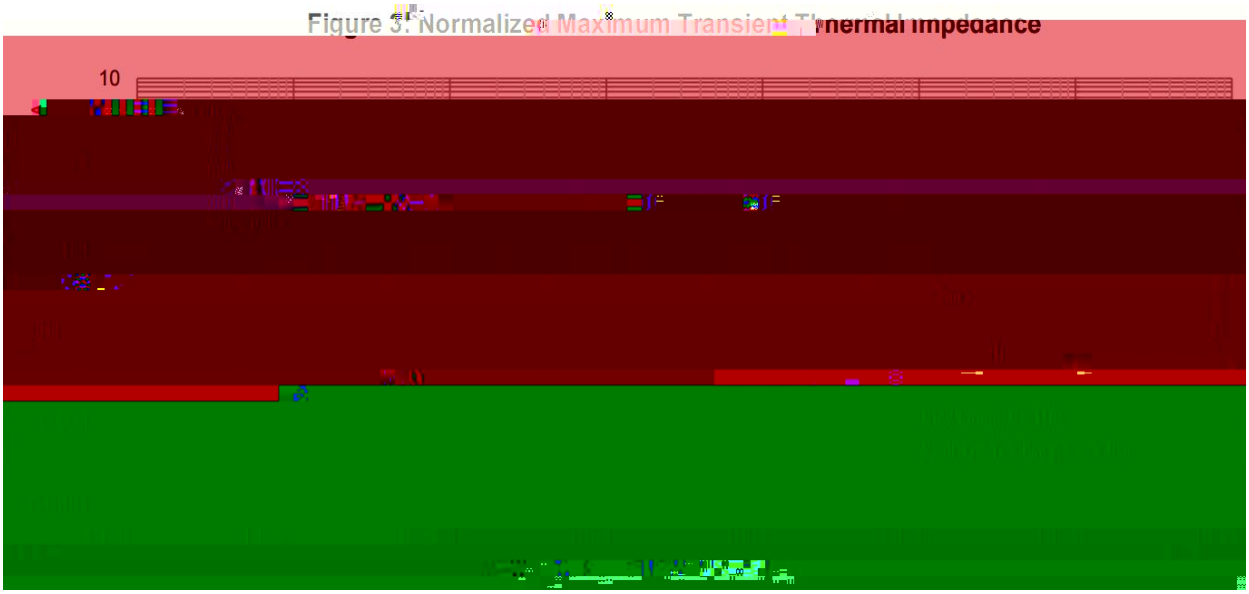
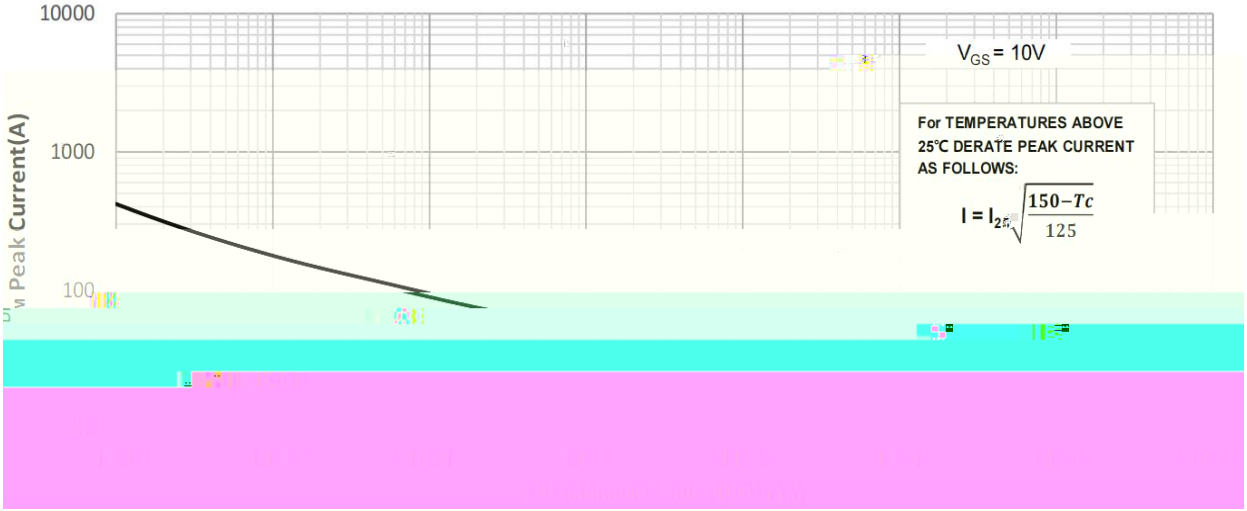



Figure 4: Peak Current Capacity



## Ratings and Characteristic Curves

Figure 5: Output Characteristics

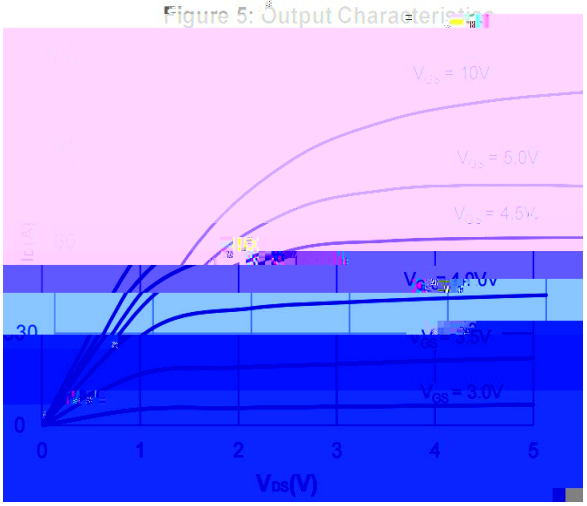



Figure 6: Typical Transfer Characteristics

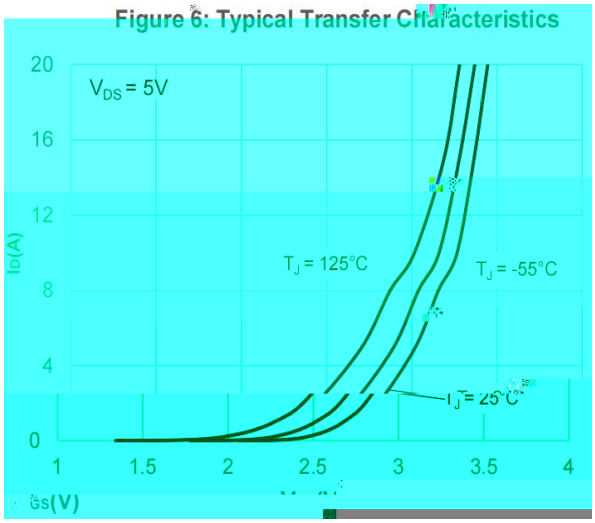



Figure 7: On-resistance vs. Drain Current

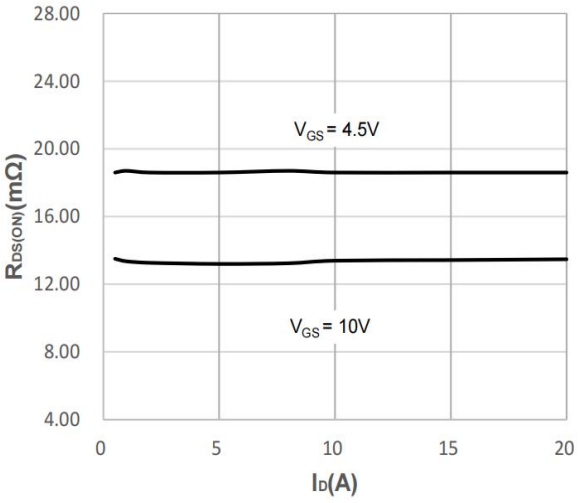



Figure 8: Body Diode Characteristics

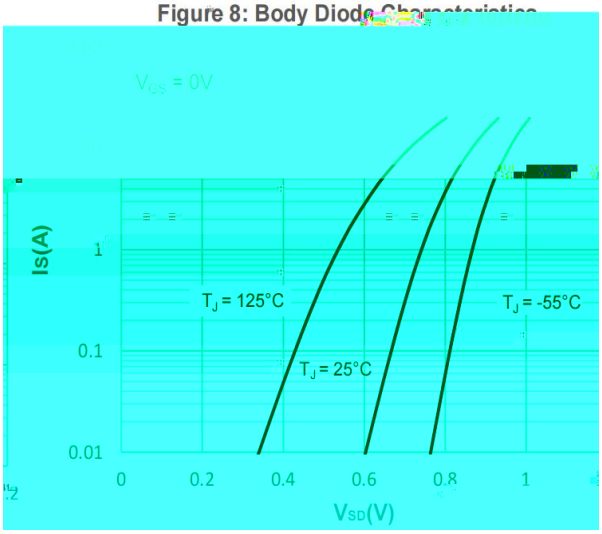



Figure 9: Gate Charge Characteristics

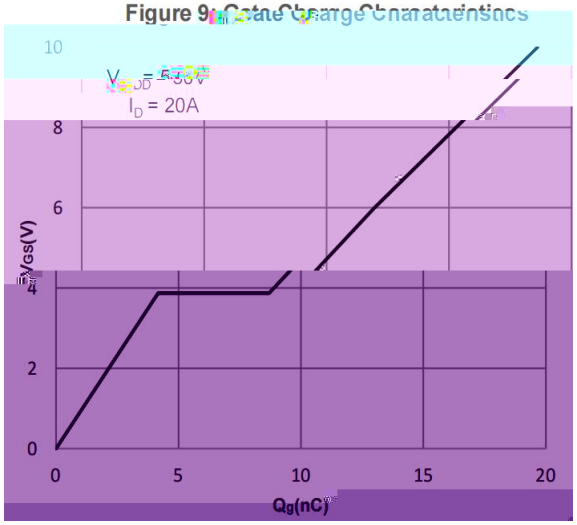



Figure 10: Capacitance Characteristics

